

MOS FIELD EFFECT TRANSISTOR 2SK3483

SWITCHING N-CHANNEL POWER MOS FET INDUSTRIAL USE

DESCRIPTION

The 2SK3483 is N-Channel MOS Field Effect Transistor designed for high current switching applications.

FEATURES

- Low On-State Resistance
 $R_{DS(on)1} = 46 \text{ m}\Omega \text{ MAX. (} V_{GS} = 10 \text{ V, } I_D = 14 \text{ A)}$
 $R_{DS(on)2} = 53 \text{ m}\Omega \text{ MAX. (} V_{GS} = 4.5 \text{ V, } I_D = 14 \text{ A)}$
- Low C_{iss} : $C_{iss} = 2300 \text{ pF TYP.}$
- Built-in Gate Protection Diode
- TO-251/TO-252 package

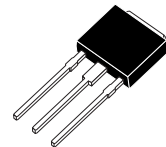
ORDERING INFORMATION

PART NUMBER	PACKAGE
2SK3483	TO-251
2SK3483-Z	TO-252

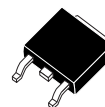
ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

Drain to Source Voltage	V_{DSS}	100	V
Gate to Source Voltage	V_{GSS}	± 20	V
Drain Current (DC)	$I_{D(DC)}$	± 28	A
Drain Current (Pulse) ^{Note1}	$I_{D(pulse)}$	± 112	A
Total Power Dissipation ($T_c = 25^\circ\text{C}$)	P_T	40	W
Total Power Dissipation ($T_A = 25^\circ\text{C}$)	P_T	1.0	W
Channel Temperature	T_{ch}	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$
Single Avalanche Current ^{Note2}	I_{AS}	T.B.D. ^{Note3}	A
Single Avalanche Energy ^{Note2}	E_{AS}	T.B.D. ^{Note3}	mJ

(TO-251)



(TO-252)



Notes 1. $PW \leq 10 \mu\text{s}$, Duty cycle $\leq 1\%$

2. Starting $T_{ch} = 25^\circ\text{C}$, $R_G = 25 \Omega$, $V_{GS} = 20 \text{ V} \rightarrow 0 \text{ V}$

3. T.B.D. : To be determined

THERMAL RESISTANCE

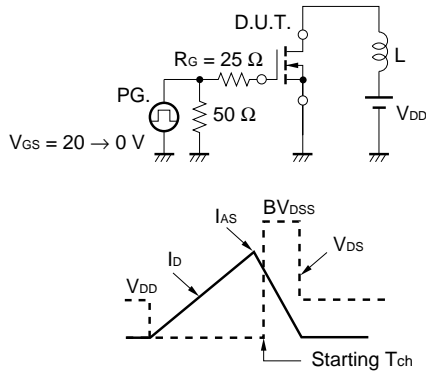
Channel to Case	$R_{th(ch-C)}$	3.13	$^\circ\text{C/W}$
Channel to Ambient	$R_{th(ch-A)}$	125	$^\circ\text{C/W}$

The information contained in this document is being issued in advance of the production cycle for the device. The parameters for the device may change before final production or NEC Corporation, at its own discretion, may withdraw the device prior to its production.
 Not all devices/types available in every country. Please check with local NEC representative for availability and additional information.

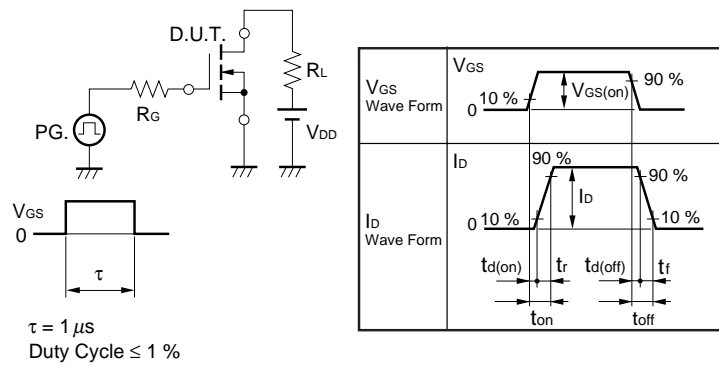
ELECTRICAL CHARACTERISTICS (T_A = 25°C)

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Drain to Source On-state Resistance	R _{DS(on)1}	V _{GS} = 10 V, I _D = 14 A		36	46	mΩ
	R _{DS(on)2}	V _{GS} = 4.5 V, I _D = 14 A		39	53	mΩ
Gate to Source Cut-off Voltage	V _{GS(off)}	V _{DS} = 10 V, I _D = 1 mA	1.5	2.0	2.5	V
Forward Transfer Admittance	y _{fs}	V _{DS} = 10 V, I _D = 14 A	16	32		S
Drain Leakage Current	I _{DSS}	V _{DS} = 100 V, V _{GS} = 0 V			10	μA
Gate to Source Leakage Current	I _{GSS}	V _{GS} = ±20 V, V _{DS} = 0 V			±10	μA
Input Capacitance	C _{iss}	V _{DS} = 10 V		2300		pF
Output Capacitance	C _{oss}	V _{GS} = 0 V		230		pF
Reverse Transfer Capacitance	C _{rss}	f = 1 MHz		120		pF
Turn-on Delay Time	t _{d(on)}	I _D = 14 A		17		ns
Rise Time	t _r	V _{GS(on)} = 10 V		10		ns
Turn-off Delay Time	t _{d(off)}	V _{DD} = 50 V		55		ns
Fall Time	t _f	R _G = 1 Ω		9.0		ns
Total Gate Charge	Q _G	I _D = 28 A		42		nC
Gate to Source Charge	Q _{GS}	V _{DD} = 80 V		7.0		nC
Gate to Drain Charge	Q _{GD}	V _{GS(on)} = 10 V		12		nC
Body Diode Forward Voltage	V _{F(S-D)}	I _F = 28 A, V _{GS} = 0 V		1.0		V
Reverse Recovery Time	t _{rr}	I _F = 28 A, V _{GS} = 0 V		88		ns
Reverse Recovery Charge	Q _{rr}	di/dt = 100 A/μs		170		nC

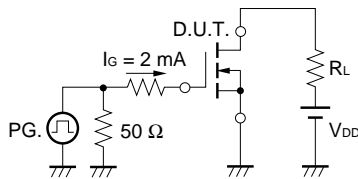
TEST CIRCUIT 1 AVALANCHE CAPABILITY



TEST CIRCUIT 2 SWITCHING TIME

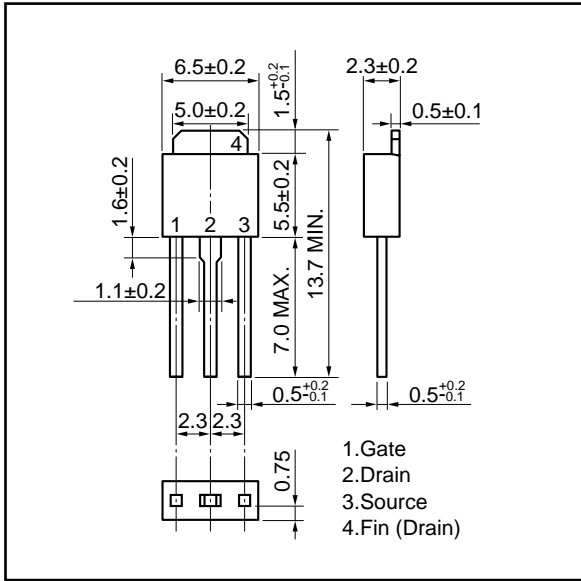


TEST CIRCUIT 3 GATE CHARGE

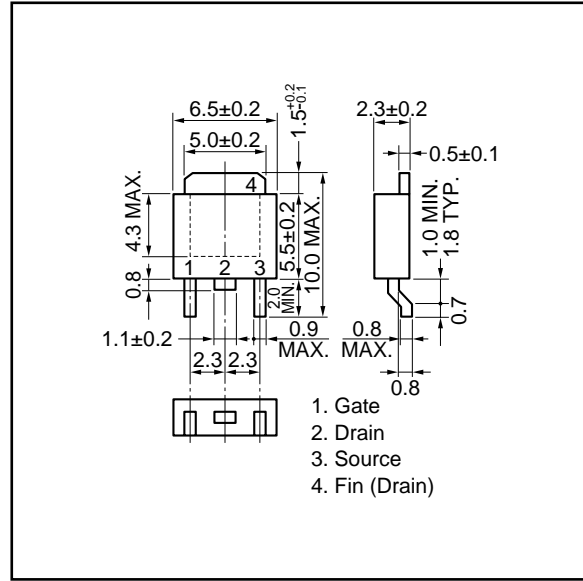


PACKAGE DRAWINGS (Unit : mm)

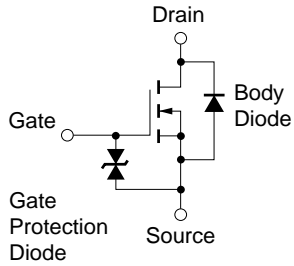
1) TO-251 (MP-3)



2) TO-252 (MP-3Z)



EQUIVALENT CIRCUIT



Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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